

INTRODUCTION TO SMART SENSING TECHNOLOGY FOR AI (AEI2206)

Time Allotted : 2½ hrs

Full Marks : 60

Figures out of the right margin indicate full marks.

*Candidates are required to answer Group A and
any 4 (four) from Group B to E, taking one from each group.*

Candidates are required to give answer in their own words as far as practicable.

Group – A

1. Answer any twelve:

12 × 1 = 12

Choose the correct alternative for the following

- (i) Strain gauge is used to measure
 - (a) Stress
 - (b) Force
 - (c) Pressure
 - (d) All of the above
- (ii) A capacitive humidity sensor works based on change in
 - (a) Distance between plates
 - (b) Area between plates
 - (c) Dielectric between plates
 - (d) None of these.
- (iii) Which of the following is the example of active transducer?
 - (a) LVDT
 - (b) Thermocouple
 - (c) Resistive potentiometer
 - (d) Strain gauge
- (iv) LVDT has
 - (a) Two primary coils connected in phase and a secondary coil
 - (b) Two primary coils connected in opposition and a secondary coil
 - (c) One primary coil and two secondary coils connected in phase
 - (d) One primary coil and two secondary coils connected in phase opposition
- (v) Example of natural piezoelectric crystal material is
 - (a) Lithium Sulphate
 - (b) Barium Titanate
 - (c) Ammonium di-hydrogen Phosphate
 - (d) Rochelle salt
- (vi) For a Hall Effect element having thickness t and current I , the relation between Hall voltage V_H and magnetic flux density B is given by,
 - (a) $R_H = V_H \cdot t / (I \cdot B)$
 - (b) $R_H = V_H \cdot t \cdot I \cdot B$
 - (c) $R_H = V_H \cdot I / (t \cdot B)$
 - (d) $R_H = V_H \cdot t \cdot I / B$
- (vii) Which of the following is not a self-generating type of transducer.
 - (a) RTD
 - (b) Thermocouple
 - (c) Piezo-electric crystal
 - (d) Photo-voltaic cell

- (viii) The RTD, assigned PT_{100} , refers to has resistance
 (a) $100\ \Omega$ at 100°C (b) $100\ \Omega$ at 0°C
 (c) $0\ \Omega$ at 0°C (d) $0\ \Omega$ at 100°C
- (ix) Process of using strong acid to cut into the unprotected parts of the metal surface to create a design is known as
 (a) Patterning (b) Etching
 (c) Deposition (d) None of the above
- (x) Working of gyroscope is based on
 (a) Centrifugal force (b) Centripetal force
 (c) Coriolis force (d) Gravitational force

Fill in the blanks with the correct word

- (xi) The expression of gauge factor for a strain gauge is _____.
- (xii) Ultrasonic transducer can be built with _____ type of transducer
- (xiii) Resistance of the thermistors varies _____ with temperature.
- (xiv) Operation of photodiode is confined in _____ quadrant of the diode V-I characteristics.
- (xv) MEMS take advantage of silicon's mechanical and _____ properties.

Group - B

2. (a) Derive the expression of gauge factor for a resistive strain gauge. State two properties of strain gauge material. [[CO1](Analyse/IOCQ)]
 (b) Describe a scheme to measure angular displacement using potentiometer type transducer and hence find the expression for sensitivity. [[CO1](Analyse/IOCQ)]
 (c) Define relative error and precision. [[CO1](Understand/LOCQ)]
- (4 + 2) + (3 + 1) + 2 = 12**
3. (a) Draw the schematic for load cell with necessary signal conditioning circuit. [[CO1](Understand/LOCQ)]
 (b) With a neat diagram explain the operation of a capacitive type microphone. [[CO1](Evaluate/HOCQ)]
 (c) Define Range, span and threshold. [[CO2](Remember/IOCQ)]
- 5 + 4 + 3 = 12**

Group - C

4. (a) Define piezoelectric effect. State example of one natural crystal and one synthetic crystal that shows piezoelectric effect. [[CO2](Analyse/IOCQ)]
 (b) A LVDT is used for measuring the deflection of a bellows element. The sensitivity of LVDT set up is $8\ \text{Volt/mm}$. The bellows element is deflected by $0.15\ \text{mm}$ for a pressure of $0.2 \times 10^6\ \text{N/m}^2$. Determine the sensitivity of the LVDT in Volt/N/m^2 and the pressure when the voltage output of LVDT is $2.5\ \text{Volt}$. [[CO2](Evaluate/HOCQ)]

- (c) Describe the operation of an inductive transducer used to measure pressure with a schematic diagram. [[CO2](Analyze/IOCQ)]
(2 + 2) + (2 + 2) + 4 = 12
5. (a) What is Hall field? Explain how Hall field is developed in a Hall element. [[CO3](Understand/LOCQ)]
 (b) Design a scheme for non-contact type current measurement system using Hall Effect transducer. [[CO3](Create/HOCQ)]
 (c) How can ultrasonic transducers be used to measure liquid level in a tank? [[CO3](Analyze/IOCQ)]
(1 + 4) + 4 + 3 = 12

Group - D

6. (a) An RTD having resistance 100 ohms at 0°C is connected to an arm of a Wheatstone bridge circuit having supply voltage 5 Volt. Each of the other three resistances is 100ohms. What will be the voltage output for the temperature 120°C. The temperature coefficient of the RTD material is 0.00385/°C. [[CO4] (Evaluate/HOCQ)]
 (b) Show the construct of a wire wound type RTD. Draw the characteristic of Pt₁₀₀ RTD. [[CO4] (Remember/LOCQ)]
 (c) Mention and explain one application of PTC type thermistor. [[CO4] (Apply/IOCQ)]
5 + (2 + 2) + 3 = 12
7. (a) What do you mean by dissipation constant of RTD as 25 mW/°C? [[CO4](Analyze/IOCQ)]
 (b) Draw the signal conditioning circuit for 3-wire RTD and hence find the expression for the output voltage. [[CO4](Create/HOCQ)]
 (c) For a certain thermistor, $\beta = 4000$ K and the resistance at 25°C is known to be 10 K Ω . The thermistor is used for temperature measurement and the resistance measured is as 990 Ω . Calculate the measured temperature. [[CO4](Evaluate/HOCQ)]
2 + (2 + 3) + 5 = 12

Group - E

8. (a) Explain working of piezoresistive micro-accelerometers with necessary circuit diagram. [[CO6](Create/HOCQ)]
 (b) How do smart sensors differs from ordinary sensors? Hence draw the structure of smart sensor. [[CO6](Analyze/IOCQ)]
 (c) State the features of a smart transmitter. [[CO6](Remember/LOCQ)]
4 + (2 + 3) + 3 = 12
9. (a) Explain working of MEMS magnetometer with necessary schematic diagram. [[CO6](Analyze/HOCQ)]
 (b) What do you mean by sensor network? Draw and describe the block diagram for the same. [[CO6](Remember/LOCQ)]

(c) State one application of MEMS sensor in the medical field.

[[CO6)(Apply/IOCQ)]

5 + (2 + 4) + 1 = 12

Cognition Level	LOCQ	IOCQ	HOCQ
Percentage distribution	26.04	36.46	37.50